

Insulated-Gate Bipolar Transistor in a TO-3P Plastic Package.

Built in fast recovery diode, Saturation voltage positive temperature coefficient, High reliability and thermal stability parameters, good agreement, RoHS product.

/ Absolute Maximum Ratings(Ta=25)

Parameter	Symbol	Rating	Unit
Collector-emitter voltage	V_{CES}	600	V
Gate-emitter voltage	V_{GES}	± 20	V
Collector current@ $T_C=25$	I_C	120	A
Collector current@ $T_C=100$		60	A
Collector peak current, T_P limited by T_{JMAX}	I_{CM}	180	A
Diode forward current@ $T_C=100$	I_F	30	A
Diode maximum forward current	I_{FM}	60	A
Power dissipation($T_C=25$)	P_D	310	W
Power dissipation($T_C=100$)		125	W
Operating junction and storage temperature range	T_J, T_{stg}	-55 155	
Maximum temperature for soldering	T_L	260	
IGBT thermal resistance,junction-case	$R_{th(j-c)}$	0.4	/W
Diode thermal resistance,junction-case	$R_{th(j-c)}$	1.2	/W
Thermal resistance,junction-ambient	$R_{th(j-a)}$	40	/W

/ Electrical Characteristics(Ta=25)

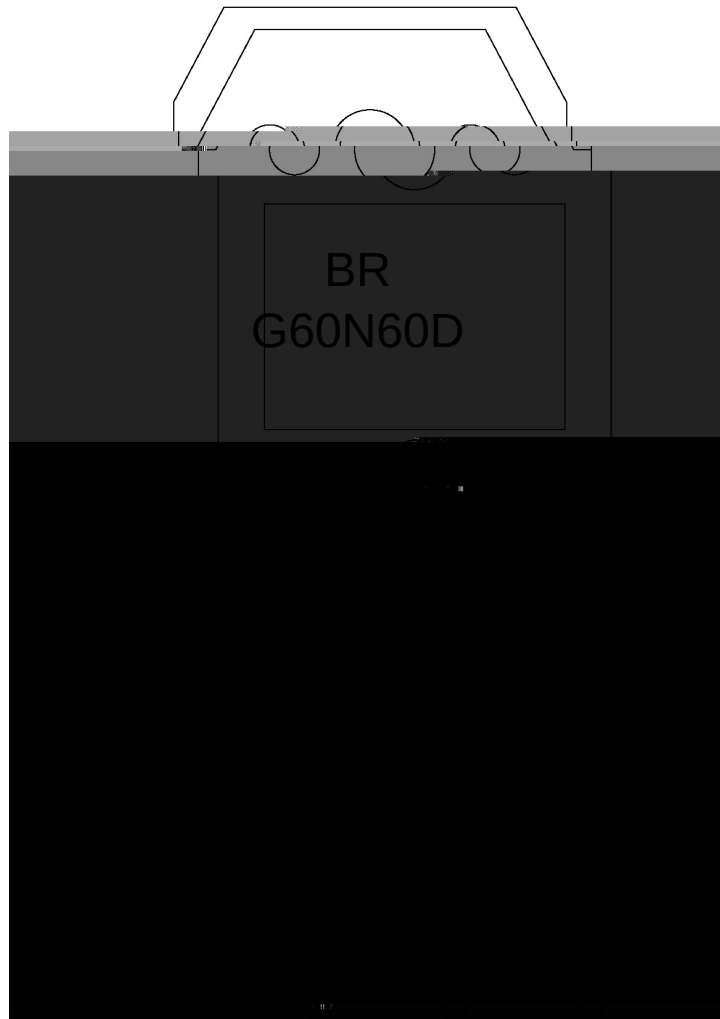
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-emitter breakdown voltage	V_{CES}	$V_{GE}=0V$ $I_{CE}=1.0mA$	610	-	-	V
Zero gate voltage Collector current	I_{CES}	$V_{GE}=0V$ $V_{CE}=650V$	-	-	4	μA
Gate-body leakage current	I_{GES}	$V_{GE}=\pm 20V$ $V_{CE}=0V$	-	-	± 100	nA
Gate threshold voltage	$V_{GE(th)}$	$I_C=0.8mA$ $V_{CE}=V_{GE}$	4	5.0	6	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=60A$ $V_{GE}=15V$	-	2.1	2.9	V
Input capacitance	C_{ies}	$V_{CE}=25V$ $f=1MHz$ $V_{GE}=0V$	-	5150	-	pF
Output capacitance	C_{oes}		-	300	-	
Reverse transfer capacitance	C_{res}		-	65	-	

/ Electrical Characteristics(Ta=25)

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Input capacitance	C_{ies}	$V_{CE}=25V$ $V_{GE}=0V$ $f=1MHz$	-	5150	-	pF
Output capacitance	C_{oes}		-	300	-	
Reverse transfer capacitance	C_{res}		-	65	-	
Turn-on delay time	$t_{d(ON)}$	$V_{CE}=400V$ $I_C=60A$, $R_G=3\Omega$ $V_{GE}=0/15V$ Inductive Load	-	35	-	ns
Rise time	t_r		-	35	-	
Turn-off delay time	$t_{d(OFF)}$		-	107	-	
Fall time	t_f		-	36	-	
Turn-On Switching Loss	E_{on}		-	2.05		mJ
Turn-Off Switching Loss	E_{off}		-	1.11		
Total Switching Loss	E_{ts}		-	3.16		
Total gate charge	Q_G	$V_{CE}=480V$ $I_C=60A$ $V_{GE}=15V$	-	135	-	nC
Diode forward voltage	V_F	$I_F=60A$	-	1.5		V
Reverse recovery time	T_{rr}	$V_R=400V$ $I_F=30A$ $di/dt=500A/\mu S$	-	60		ns
Diode Peak Reverse Recovery Current	I_{rr}		-	12		A
Reverse recovery charge	Q_{rr}		-	0.4		μC

/ Package Dimensions

/ Marking Instructions



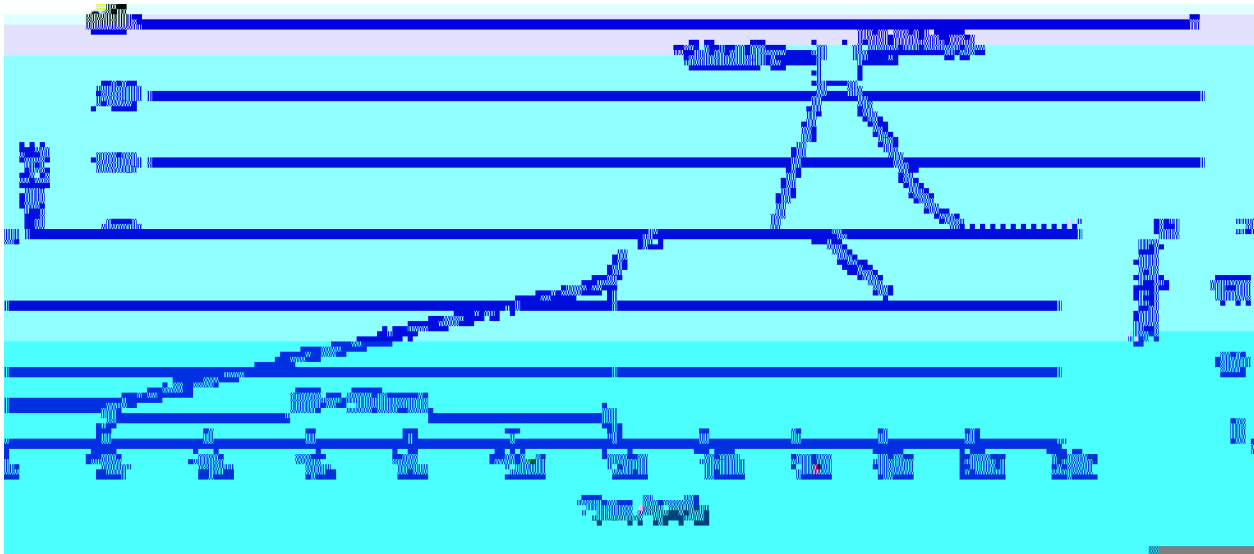
Note:

BR: Company Code.

G60N60D: Product Type.

****: Lot No. Code, code change with Lot No.

() / Temperature Profile for Dip Soldering(Pb-Free)



Note:

- 1

25 150

60 90sec;
- 2

255 5

5 0.5sec;
- 3

2 10

/sec.
- 1.Preheating:25~150

, Time:60~90sec.
- 2.Peak Temp.:255 5

, Duration:5 0.5sec.
3. Cooling Speed: 2~10

/sec.

/ Resistance to Soldering Heat Test Conditions

270 5

10 1 sec.

Temp.:270±5

Time:10±1 sec

/ Packaging SPEC.

/ TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	只 套管	套管 盒	只 盒	盒 箱	只 箱	套管	盒	箱
								x x

/ Notices